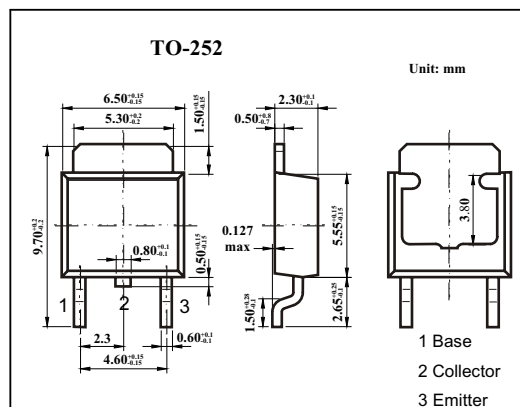


NPN Silicon Power Transistor

2SD882

■ Features

- Collector Power Dissipation: $P_c=1.25W$
- Collector Current: $I_c=3A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current to Continuous	I_c	3	A
Collector Dissipation	P_c	1.25	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_c=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_c=10\text{ mA}, I_B=0$	30			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=100\mu A, I_c=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{ V}, I_E=0$			1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=30\text{ V}, I_B=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{ V}, I_c=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{ V}, I_c=1\text{ A}$	60		400	
		$V_{CE}=2\text{ V}, I_c=100\text{ mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=2\text{ A}, I_B=0.2\text{ A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c=2\text{ A}, I_B=0.2\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{ V}, I_c=0.1\text{ mA}, f=10\text{ MHz}$	50			MHz

■ h_{FE} Classification

Rank	R	Q	P	GR
h_{FE}	60~120	100~200	160~320	200~400

■ Marking

Marking	D882
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